ABSTRACT OF THE DISCLOSURE

A semiconductor light emitting device comprises: a substrate; an n-type layer provided on the substrate and made of a nitride semiconductor material; a multiple quantum well structure active layer including a plurality of well layers each made of $In_xGa_{(1-x-y)}Al_yN$ ($0 \leq x$, $0 \leq y$, $x+y<1$) and a plurality of barrier layers each made of $In_sGa_{(1-s-t)}Al_tN$ ($0 \leq s$, $0 \leq t$, $s+t<1$), the multiple quantum well structure active layer being provided on the n-type layer; and a p-type layer provided on the multiple quantum well structure active layer and made of a nitride semiconductor material. The p-type layer contains hydrogen, and the hydrogen concentration of the p-type layer is greater than or equal to about 1×10^{16} atoms/cm^3 and less than or equal to about 1×10^{19} atoms/cm^3.